

in Electronics

Volume 5

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Reliability Series

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A. T. CULBERTSON  
Brig Gen, USAF  
Commander

PREFACE

The fifth in a series of annual symposia on the Physics of Failure in Electronics convened at Battelle Memorial Institute in Columbus, Ohio, on November 15, 16, and 17, 1966. It was jointly sponsored by Rome Air Development Center and the Battelle-Columbus Laboratories. There were about 535 individuals in attendance, thirty of them from seven foreign countries.

Centering almost exclusively on scientific inquiry into material processes and phenomena influencing the degradation and failure of solid state electronic devices and related structures, the Symposium technical program contained two invited papers, twenty-seven contributed papers, and seven late-news papers.

The organization of the invited and contributed papers in the Proceedings corresponds to their order of presentation in the seven technical sessions of the Symposium. The few papers for which manuscripts were not available for publication are represented by abstracts only. While the late-news papers are not published herein, we wish to acknowledge the valuable contribution of the authors of those papers to the success of the Symposium. Thus, the titles and authors of the late-news papers presented are listed at the end of the book.

Welcoming remarks were presented by David G. Minton, Jr., Director, Columbus Laboratories, Battelle Memorial Institute. The opening address was given by John B. Walsh, Deputy for Research, Office of the Assistant Secretary of the Air Force (R&D). Dr. John R. Pierce, Executive Director, Research, Communications Sciences Division, Bell Telephone Laboratories, delivered a banquet address entitled "The Need for Reliability in Communication Systems--A Look at the Future".

To these people and to the committee members and session moderators listed on the next page we owe a debt of gratitude. Acknowledgement for diligent and faithful service to the Symposium and its affairs is also due to Mrs. Michele Kershner, Miss Faye Vance, and many other members of the staff of the Battelle-Columbus Laboratories.

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TABLE OF CONTENTS

Contents

Page

Opening Address - John B. Walsh, Deputy for Research,  
Office of the Assistant Secretary of the Air  
Force (R&D)..... xi

SECTION I - TESTING AND ANALYSIS

Some Unifying Concepts in Reliability Physics,  
Mathematical Models, and Statistics\*..... 1

R. E. Thomas

Progressive Failure Mechanisms of a Commercial  
Silicon Signal Diode..... 18

J. F. Schenck

SECTION II A - INVESTIGATIVE TECHNIQUES

Optical Scanning Techniques for Semiconductor Device  
Screening and Identification of Surface and Junction  
Phenomena..... 37

C. N. Potter  
D. E. Sawyer

Photoresponse Mapping of Semiconductors..... 51

J. R. Haberer

Infrared Analysis Technique for Determining  
Aluminum-Phosphosilicate Reaction..... 83

M. M. Nanda  
E. A. Corl  
S. L. Silverman

A Reliability Screening Procedure for  
Integrated Circuits..... 101

W. Gill  
W. Workman

SECTION II B - FILMS AND FILM DEVICES

Load-Life Tests of Cermet Thin-Film Resistors..... 143

P. Schable  
J. Overmeyer  
R. L. Glang

The Interaction of Oxygen with Clean Chromium Films  
and Its Influence on the Electrical Film Properties..... 158

W. A. Crossland  
H. T. Roettgers

\*Invited paper.

TABLE OF CONTENTS (Continued)

Contents	Page
Stability of Thin-Film Transistors.....	183
J. J. Fabula	
R. L. Schelhorn	
M. L. Topfer	
<b>SECTION III - SiO<sub>2</sub> AND SILICON SURFACES</b>	
The Oxide-Silicon Interface*.....	199
R. P. Donovan	
Positive and Negative Ion Motion in Thermal Oxide on Silicon by Radiochemical and MOS Analysis.....	232
A. B. Kuper	
C. J. Slabinski	
E. Yon	
Failure Mechanisms in Passivated p <sup>+</sup> -n Junctions Under Temperature and Bias Stress.....	244
Takashi Tokuyama	
Clean MOS Systems.....	265
H. G. Carlson	
G. A. Brown	
D. E. Meyer	
Migration of Gold and Nickel Ions in Films of SiO <sub>2</sub> .....	292
J. R. Szadon	
R. M. Handy	
<b>SECTION IV A - RADIATION EFFECTS</b>	
Surface Effects of Radiation on MOS Transistors.....	311
Barbara W. Kuhne	
Degradation of MIS Devices Under Electron Bombardment.....	328
K. H. Zaininger	
Proton Irradiation Effects in MOS and Junction Field- Effect Transistors and Integrated Circuits.....	349
F. R. Bryant	
C. L. Fales, Jr.	
R. A. Breckenridge	
Temporary Neutron Damage in Transistors.....	373
B. Barnett	
L. M. Langsam	
S. L. Rosen	
C. B. Schoch	
D. A. Schow	

\*Invited paper.

TABLE OF CONTENTS (Continued)

Contents	Page
Radiation Testing of Linear Microcircuits.....	391
J. D. Lieux	
<b>SECTION IV B - BULK EFFECTS</b>	
Degradation of Gallium Arsenide Laser Diodes.....	423
H. T. Minden	
Second Breakdown in Silicon Power Transistors at High Collector Voltages.....	424
R. M. Scarlett	
G. F. Hardy	
Effect of Thermal Oxidation Dislocation Enhancement on Silicon and a Proposed Mode of Propagation.....	444
G. Onodera	
P. Walker	
Studies of the Uniformity of Avalanche Breakdown by Means of Low Frequency Noise Measurements.....	447
R. H. Haltz	
The Significance of Dislocation Density and Impurity Inhomogeneities to the Breakdown Characteristics of Production Run Planar Devices.....	462
D. R. Colton	
P. Dakin	
R. Falconer	
A. Slavin	
<b>SECTION V - BONDS AND INTERCONNECTS</b>	
Prevention of Stress-Corrosion Failure in Iron-Nickel- Cobalt Alloy Semiconductor Device Leads.....	477
M. J. Elkind	
H. E. Hughes	
The Failure of Thin Aluminum Current Carrying Strips on Oxidized Silicon.....	496
I. A. Blech	
H. Sello	
A Plague-Free Aluminum-Gold System on Silicon Integrated Circuits.....	506
M. A. Schuster	
W. J. Lytle	

TABLE OF CONTENTS (Continued)

Contents	Page
Correlation of Electrical, Microstructural, and Chemical Properties of Heat-Treated Platinum- Silicon Contact Devices.....	519
R. Silverman	
N. Cerniglia	
Microbonds for Hybrid Microcircuits.....	534
A. R. Riben	
S. L. Sherman	
W. V. Lane	
R. R. Geisler	
LIST OF LATE-NEWS PAPERS.....	557